

## SMALL SIGNAL SWITCHING DIODE

**VOLTAGE RANGE: 50 V**  
**CURRENT: 150 m A**

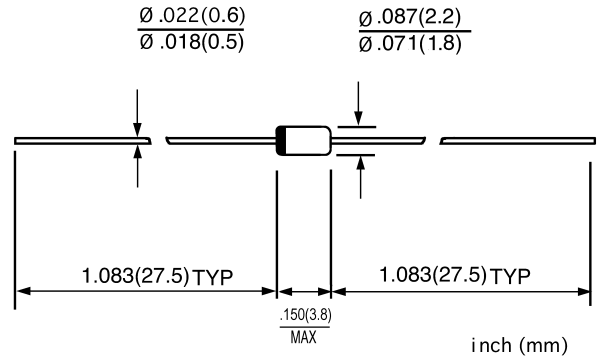
### FEATURES

- Silicon epitaxial planar diode
- High speed switching diode
- 500 mW power dissipation

### MECHANICAL DATA

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams

DO - 35



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

#### MAXIMUM RATINGS

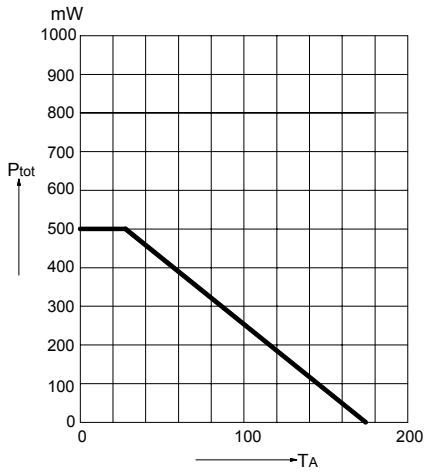
		1N4150	UNITS
Reverse voltage	$V_R$	50	V
Peak reverse voltage	$V_{RM}$	50	V
Average forward rectified current $V_R=0V$	$I_O$	150	mA
Forward surge current at $t=1\mu s$	$I_{FSM}$	4.0	A
Power dissipation	$P_{tot}$	500	mW
Thermal resistance junction to ambient	$R_{thja}$	500	K/W
Junction temperature	$T_j$	175	
Storage temperature range	$T_{STG}$	-65 --- + 175	

#### ELECTRICAL CHARACTERISTICS

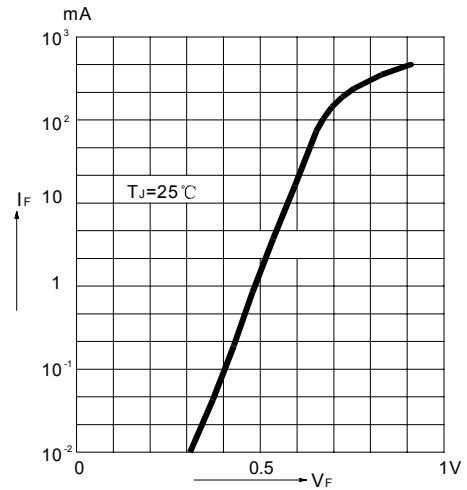
		MIN.	MAX.	UNITS
Forward voltage at $I_F=1mA$	$V_F$	0.54	0.62	V
$I_F=10mA$		0.66	0.74	
$I_F=50mA$		0.76	0.86	
$I_F=100mA$		0.82	0.92	
$I_F=200mA$		0.87	1.0	
Leakage current @ $V_R=50V, T_J=25$	$I_R$	-	0.1	$\mu A$
$V_R=50V, T_J=150$		-	100	
Capacitance at $V_R=0V, f=1MHz, V_{HF}=50mV$	$C_{tot}$	-	2.5	pF
Reverse recovery time $I_F=I_R=(10to100mA), i_R=0.1 \times I_R$ $R_L=100$	$t_{rr}$	-	4.0	ns

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**FIG.1 – ADMISSIBLE POWER DISSIPATION  
VERSUS AMBIENT TEMPERATURE**



**FIG.2 – FORWARD CHARACTERISTICS**



**FIG.3 – LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE**

